

### Description

The IRF7406PBF uses advanced trench

technology to provide excellent  $R_{\text{DS}(\text{ON})},$  low gate

charge and operation with gate voltages as low as

2.5V. This device is suitable for use as a

Battery protection or in other Switching application.

#### **General Features**

V<sub>DS</sub> =-30V I<sub>D</sub> =-9A

 $R_{DS(ON)} < 20m\Omega @ V_{GS}=10V$ 

## Application

Battery protection

Load switch

Uninterruptible power supply

### Package Marking and Ordering Information

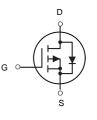
Product ID	Pack	Brand	Qty(PCS)
IRF7406PBF	SOP-8	HXY MOSFET	3000

### Absolute Maximum Ratings (Tc=25 C unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	- 30	V
VGS	Gate-Source Voltage	<u>+</u> 20	V
I <sub>D</sub> @T <sub>A</sub> =25℃	Drain Current <sup>3</sup> , V <sub>GS</sub> @ 10V	-9	А
I <sub>D</sub> @T <sub>A</sub> =70℃	Drain Current <sup>3</sup> , V <sub>GS</sub> @ 10V	-7.3	А
IDM	Pulsed Drain Current <sup>1</sup>	-50	А
P <sub>D</sub> @T <sub>A</sub> =25℃	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	50	°C/W



SOP-8



P-Channel MOSFET



## Electrical Characteristics @Tj=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-7A	-	18	20	mΩ
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A	-	32	36	mΩ
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-1	-	-3	V
<b>g</b> fs	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-7A	-	16	-	S
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-30	uA
IGSS	Gate-Source Leakage	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Qg	Total Gate Charge	I <sub>D</sub> =-7A	-	18	29	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-24V	-	3	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =-4.5V	-	10	-	nC
td(on)	Turn-on Delay Time	V <sub>DS</sub> =-15V	-	8	-	ns
tr	Rise Time	I <sub>D</sub> =-1A	-	6.6	-	ns
td(off)	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	44	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =-10V	-	34	-	ns
Ciss	Input Capacitance	V <sub>GS</sub> =0V	-	1175	1690	pF
Coss	Output Capacitance	V <sub>DS</sub> =- 25V	-	195	-	pF
Crss	Reverse Transfer Capacitance	f=1.0MHz	-	190	-	pF
Vsd	Forward On Voltage <sup>2</sup>	Is=-2.1A, V <sub>GS</sub> =0V	-	-	-1.2	V
trr	Reverse Recovery Time	Is=-7A, V <sub>GS</sub> =0V, dl/dt=100A/µs	-	28	-	ns
Qrr	Reverse Recovery Charge	7	-	18	_	nC

#### Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board, t  $\leq$ 10sec ; 125 °C/W when mounted on Min. cop



# **Typical Electrical and Thermal Characteristics (Curves)**

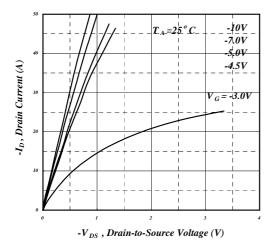


Fig 1. Typical Output Characteristics

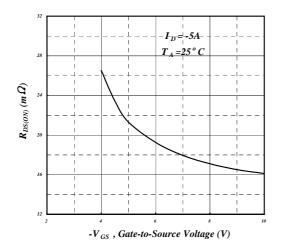


Fig 3. On-Resistance v.s. Gate Voltage

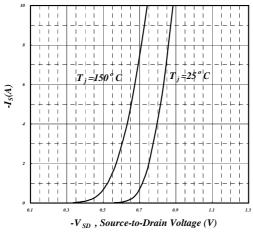


Fig 5. Forward Characteristic of Reverse Diode

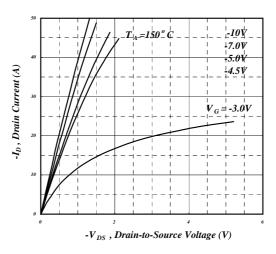


Fig 2. Typical Output Characteristics

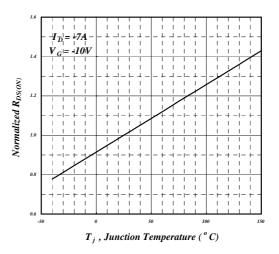


Fig 4. Normalized On-Resistance v.s. Junction Temperature

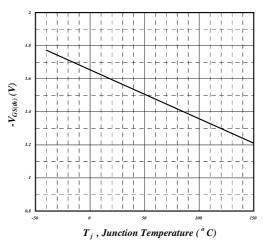
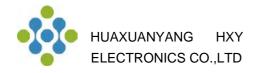


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



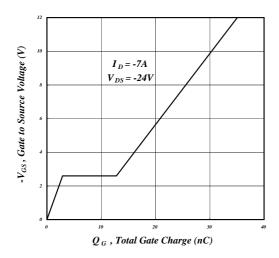


Fig 7. Gate Charge Characteristics

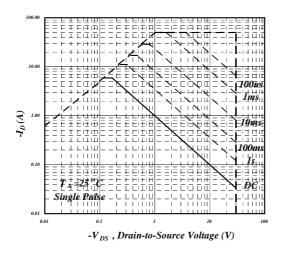


Fig 9. Maximum Safe Operating Area

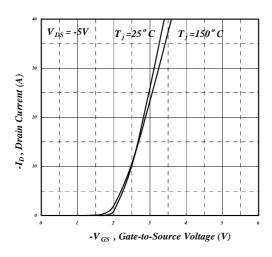


Fig 11. Transfer Characteristics

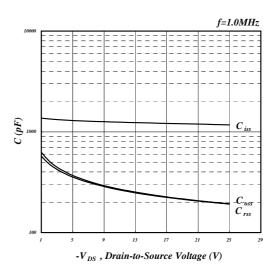


Fig 8. Typical Capacitance Characteristics

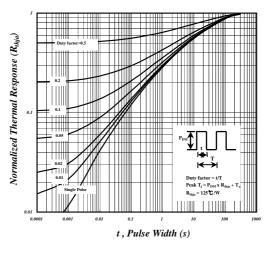


Fig 10. Effective Transient Thermal Impedance

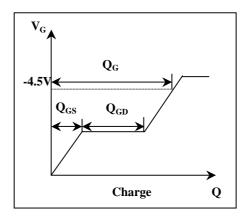
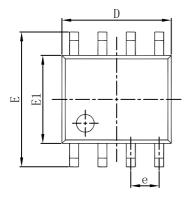
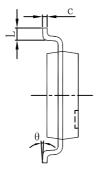


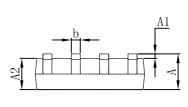
Fig 12. Gate Charge Circuit



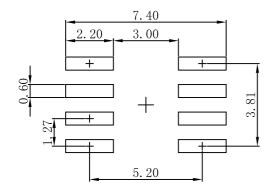
# **SOP-8 Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0.197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0 °	8°	0 °	8°	



Note: 1.Controlling dimension: in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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